Icemos Technology Ltd Product Specification 1000.509902 Issue Date 16 August 2022 15:51

Part Number	C. Aleman
Part Number	Customer

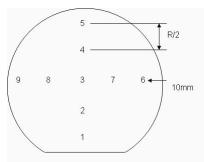
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	200.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1.0 degree	Wafer Vendor
	3.0	Notch or Flat	Notch	Wafer Vendor
	4.0	Secondary Flat Orientation	None	Wafer Vendor
	5.0	Overall Thickness	700.00 +/- 26.00 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<10.00μm	Guaranteed by Process
	7.0	Bow	<80.00μm	ADE to ASTM F534, 100%
	8.0	Warp	<80.00μm	
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	13.0	Handle Thickness	675.00 +/- 25.00 μm	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	0.01 ~ 0.02 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Lapped and etched with poly oxide seal.	Wafer Vendor
BuriedOxide	18.0	Oxide Type	None	
DeviceSilicon	19.0	Device Growth Method	FZ	Wafer Vendor
	20.0	Device Orientation	{100} +/- 1.0 degree	Wafer Vendor
	21.0	Nominal Thickness	25.00 +/- 1.00 μm	ADE single point measurement, 100%
	22.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	23.0	Device Doping Type	P	Wafer Vendor
	24.0	Device Dopant	Boron	Wafer Vendor
	25.0	Device Resistivity	>1000 Ohmcm	Wafer Vendor
	26.0	Voids	none	Bright Light, 100% (note 2)
	27.0	Scratches	10mm maximum length.	Bright Light, 100% (note 2)
	28.0	Haze	none	Bright Light, 100% (note 2)

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Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 200.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspec	ction performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall			

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overal Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information